

AMENDMENTS TO THE SPECIFICATION

Please add the following paragraphs to the BRIEF DESCRIPTION OF THE DRAWINGS section beginning on page 4, line 23:

FIG. 6 is a cross-sectional view illustrating forming the first, second and third layers according to an embodiment of the invention.

FIG. 7 is a cross-sectional view illustrating patterning the third layer according to an embodiment of the invention.

FIG. 8 is a cross-sectional view illustrating patterning of the first and second layers according to an embodiment of the invention.

Please replace the paragraph beginning on page 4, line 30, and continuing on page 5, line 7, with the following:

As shown in FIG. 6, a conductive layer for interconnections 54, a material layer for capping 56, and a material layer for stopping etching 58 are sequentially deposited on the surface of the first interlayer insulating layer 52. As shown in FIG. 7, the material layer for stopping etching 58 is patterned to form etching stoppers 58a, 58b, and 58c. Then, as shown in FIG. 8, the material layer for capping 56 and the conductive layer for interconnections 54 are patterned using the patterned material layer for stopping etching 58. As a result, interconnection layers 54, capping layers 56a, 56b, and 56c and etching stoppers 58a, 58b, and 58c are sequentially formed. The interconnection layers 54 are a metal layer containing aluminum, and the capping layers 56a, 56b, and 56c are formed of TiN, Ti/TiN or TaN. The etching stoppers 58a, 58b, 58c are formed of a material having a high etching selectivity with respect to a second interlayer insulating layer 60 which will be formed later, such as an inorganic anti-reflecting layer (ARL) or an organic anti-reflecting coat (ARC) which is typically used in a semiconductor device.